Hex Buffer

MC14049B, MC14050B

The MC14049B Hex Inverter/Buffer and MC14050B Noninverting Hex Buffer are constructed with MOS P−Channel and N−Channel enhancement mode devices in a single monolithic structure. These complementary MOS devices find primary use where low power dissipation and/or high noise immunity is desired. These devices provide logic level conversion using only one supply voltage, V_{DD}.

The input−signal high level (V_{IH}) can exceed the V_{DD} supply voltage for logic level conversions. Two TTL/DTL loads can be driven when the devices are used as a CMOS−to−TTL/DTL converter (V_{DD} = 5.0 V, $V_{OL} \le$ 0.4 V, $I_{OL} \ge$ 3.2 mA).

Note that pins 13 and 16 are not connected internally on these devices; consequently connections to these terminals will not affect circuit operation.

Features

- High Source and Sink Currents
- High−to−Low Level Converter
- Supply Voltage Range = 3.0 V to 18 V
- V_{IN} can exceed V_{DD}
- Meets JEDEC B Specifications
- Improved ESD Protection On All Inputs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

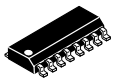
Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}	Input Voltage Range (DC or Transient)	−0.5 to +18.0	V
V_{out}	Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}	Input Current (DC or Transient) per Pin	±10	mA
I_{out}	Output Current (DC or Transient) per Pin	±45	mA
P_D	Power Dissipation, per Package (Note 1) (Plastic) (SOIC)	 825 740	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: See Figure 3.

This device contains protection circuitry to protect the inputs against damage due to high static voltages or electric fields referenced to the V_{SS} pin only. Extra precautions must be taken to avoid applications of any voltage higher than the maximum rated voltages to this high−impedance circuit. For proper operation, the ranges $V_{SS} \le V_{in} \le$ 18 V and $V_{SS} \le V_{out} \le V_{DD}$ are recommended.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

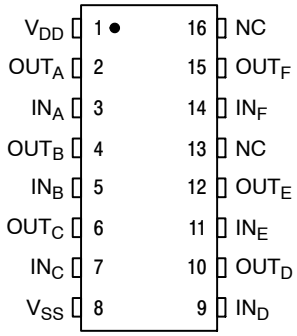


SOIC−16
D SUFFIX
CASE 751B

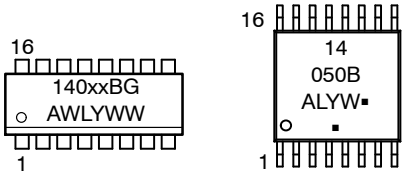


TSSOP−16
DT SUFFIX
CASE 948F

PIN ASSIGNMENT



MARKING DIAGRAMS



SOIC−16 TSSOP−16

xx	= Specific Device Code
A	= Assembly Location
WL, L	= Wafer Lot
YY, Y	= Year
WW, W	= Work Week
G or ▪	= Pb−Free Indicator

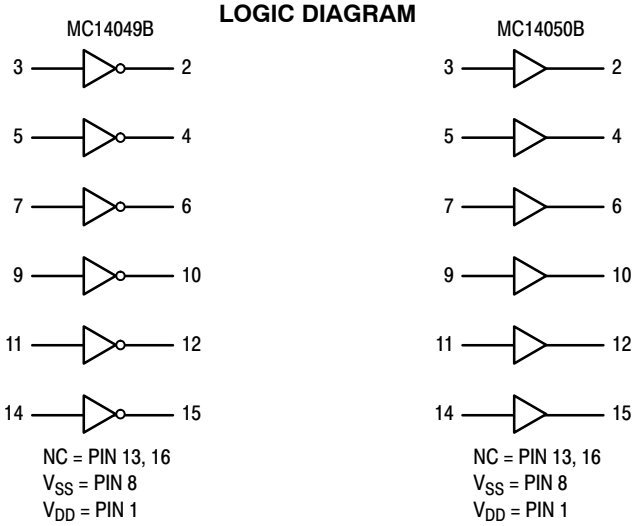
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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LOGIC DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping†
MC14049BDG	SOIC−16 (Pb−Free)	48 Units / Rail
MC14049BDR2G	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
NLV14049BDR2G*	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
MC14050BDG	SOIC−16 (Pb−Free)	48 Units / Rail
MC14050BDR2G	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
NLV14050BDR2G*	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
MC14050BDTR2G	TSSOP−16 (Pb−Free)	2500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	–55°C Min	–55°C Max	+25°C Min	+25°C Typ (Note 2)	+25°C Max	+125°C Min	+125°C Max	Unit
Output Voltage “0” Level	V_{OL}	5.0	–	0.05	–	0	0.05	–	0.05	Vdc
$V_{in} = V_{DD}$		10	–	0.05	–	0	0.05	–	0.05	
		15	–	0.05	–	0	0.05	–	0.05	
“1” Level	V_{OH}	5.0	4.95	–	4.95	5.0	–	4.95	–	Vdc
$V_{in} = 0$		10	9.95	–	9.95	10	–	9.95	–	
		15	14.95	–	14.95	15	–	14.95	–	
Input Voltage “0” Level	V_{IL}									Vdc
(V_O = 4.5 Vdc)		5.0	–	1.5	–	2.25	1.5	–	1.5	
(V_O = 9.0 Vdc)		10	–	3.0	–	4.50	3.0	–	3.0	
(V_O = 13.5 Vdc)		15	–	4.0	–	6.75	4.0	–	4.0	
“1” Level	V_{IH}									Vdc
(V_O = 0.5 Vdc)		5.0	3.5	–	3.5	2.75	–	3.5	–	
(V_O = 1.0 Vdc)		10	7.0	–	7.0	5.50	–	7.0	–	
(V_O = 1.5 Vdc)		15	11	–	11	8.25	–	11	–	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	–1.6	–	–1.25	–2.5	–	–1.0	–	
(V_{OH} = 9.5 Vdc)		10	–1.6	–	–1.30	–2.6	–	–1.0	–	
(V_{OH} = 13.5 Vdc)		15	–4.7	–	–3.75	–10	–	–3.0	–	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	3.75	–	3.2	6.0	–	2.6	–	mAdc
(V_{OL} = 0.5 Vdc)		10	10	–	8.0	16	–	6.6	–	
(V_{OL} = 1.5 Vdc)		15	30	–	24	40	–	19	–	
Input Current	I_{in}	15	–	±0.1	–	±0.00001	±0.1	–	±1.0	μAdc
Input Capacitance (V_{in} = 0)	C_{in}	–	–	–	–	10	20	–	–	pF
Quiescent Current (Per Package)	I_{DD}	5.0	–	1.0	–	0.002	1.0	–	30	μAdc
		10	–	2.0	–	0.004	2.0	–	60	
		15	–	4.0	–	0.006	4.0	–	120	
Total Supply Current (Notes 3 & 4) (Dynamic plus Quiescent, per package) (C_L = 50 pF on all outputs, all buffers switching	I_T	5.0	$I_T = (1.8\ \mu A/kHz)\ f + I_{DD}$							μAdc
		10	$I_T = (3.5\ \mu A/kHz)\ f + I_{DD}$							
		15	$I_T = (5.3\ \mu A/kHz)\ f + I_{DD}$							

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
3. The formulas given are for the typical characteristics only at +25°C
4. To calculate total supply current at loads other than 50 pF:

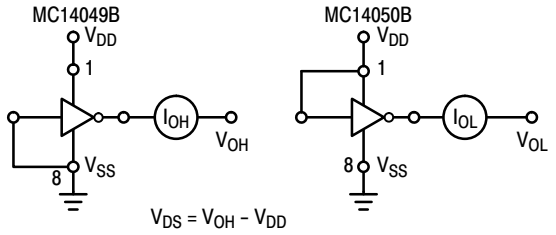
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

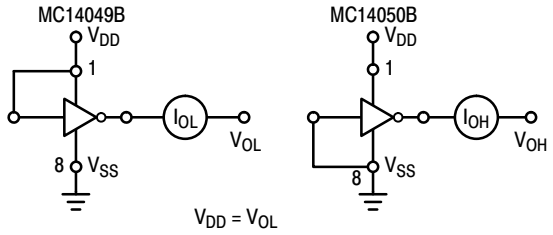
Where: I_T is in μA (per Package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency and k = 0.002.

AC SWITCHING CHARACTERISTICS (Note 5) (C_L = 50 pF, T_A = + 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t_{TLH}					ns
t_{TLH} = (0.7 ns/pF) C_L + 65 ns		5.0	–	100	160	
t_{TLH} = (0.25 ns/pF) C_L + 37.5 ns		10	–	50	80	
t_{TLH} = (0.2 ns/pF) C_L + 30 ns		15	–	40	60	
Output Fall Time	t_{THL}					ns
t_{THL} = (0.2 ns/pF) C_L + 30 ns		5.0	–	40	60	
t_{THL} = (0.06 ns/pF) C_L + 17 ns		10	–	20	40	
t_{THL} = (0.04 ns/pF) C_L + 13 ns		15	–	15	30	
Propagation Delay Time	t_{PLH}					ns
t_{PLH} = (0.33 ns/pF) C_L + 63.5 ns		5.0	–	80	140	
t_{PLH} = (0.19 ns/pF) C_L + 30.5 ns		10	–	40	80	
t_{PLH} = (0.06 ns/pF) C_L + 27 ns		15	–	30	60	
Propagation Delay Time	t_{PHL}					ns
t_{PHL} = (0.2 ns/pF) C_L + 30 ns		5.0	–	40	80	
t_{PHL} = (0.1 ns/pF) C_L + 15 ns		10	–	20	40	
t_{PHL} = (0.05 ns/pF) C_L + 12.5 ns		15	–	15	30	

5. The formulas given are for the typical characteristics only at 25°C.
6. Data labeled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.





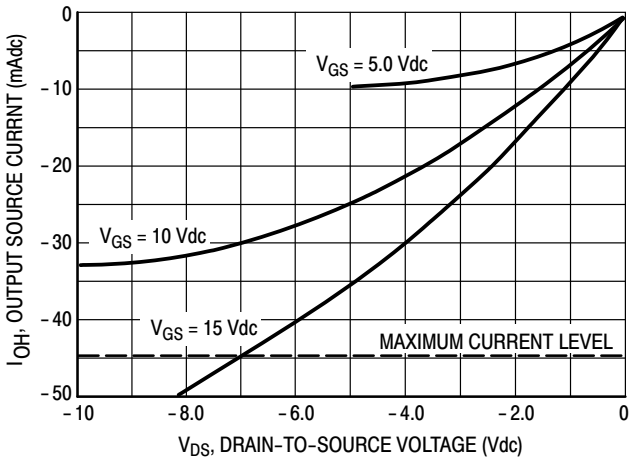


Figure 1. Typical Output Source Characteristics

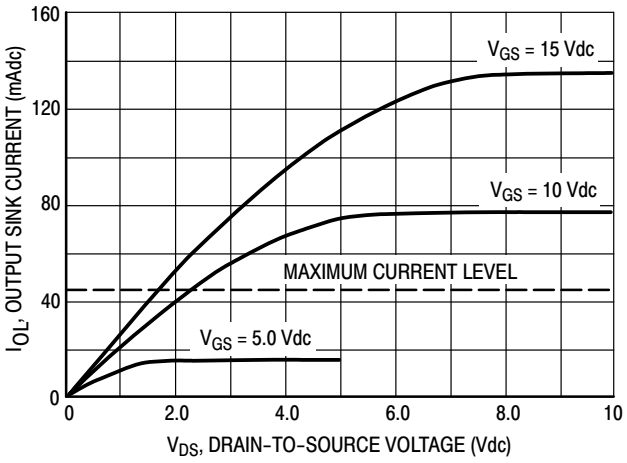


Figure 2. Typical Output Sink Characteristics

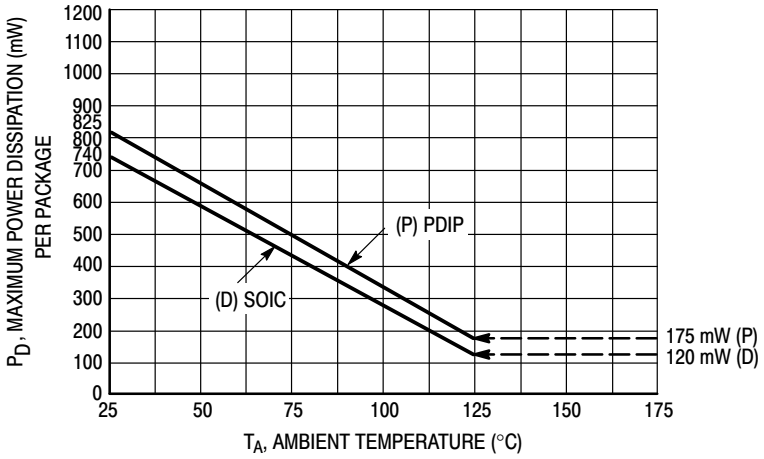


Figure 3. Ambient Temperature Power Derating

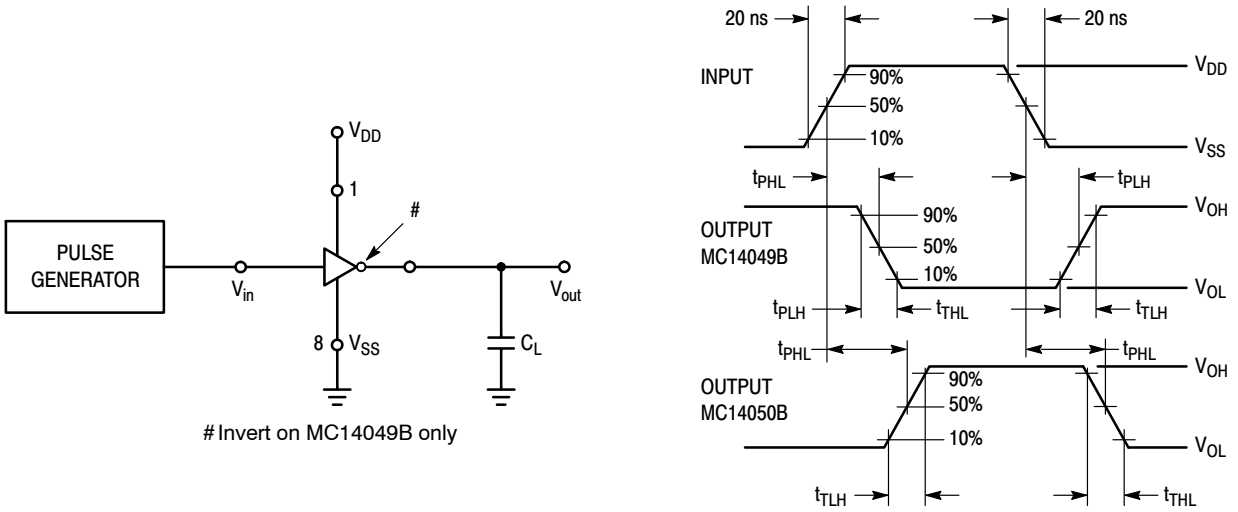
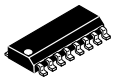


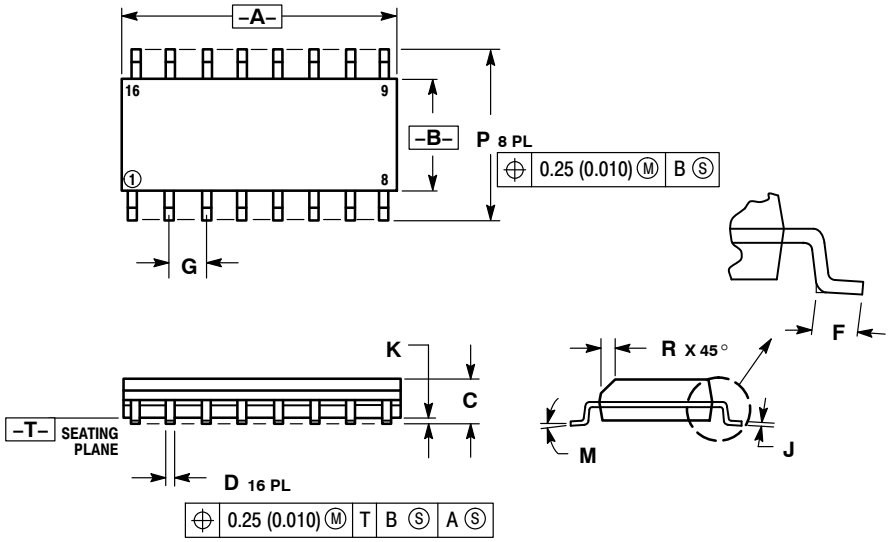
Figure 4. Switching Time Test Circuit and Waveforms



SCALE 1:1

SOIC–16
CASE 751B–05
ISSUE K

DATE 29 DEC 2006



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR
15. EMITTER
16. COLLECTOR

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION
4. CATHODE
5. CATHODE
6. NO CONNECTION
7. ANODE
8. CATHODE
9. CATHODE
10. ANODE
11. NO CONNECTION
12. CATHODE
13. CATHODE
14. NO CONNECTION
15. ANODE
16. CATHODE

STYLE 3:
PIN 1. COLLECTOR, DYE #1
2. BASE, #1
3. EMITTER, #1
4. COLLECTOR, #1
5. COLLECTOR, #2
6. BASE, #2
7. EMITTER, #2
8. COLLECTOR, #2
9. COLLECTOR, #3
10. BASE, #3
11. EMITTER, #3
12. COLLECTOR, #3
13. COLLECTOR, #4
14. BASE, #4
15. EMITTER, #4
16. COLLECTOR, #4

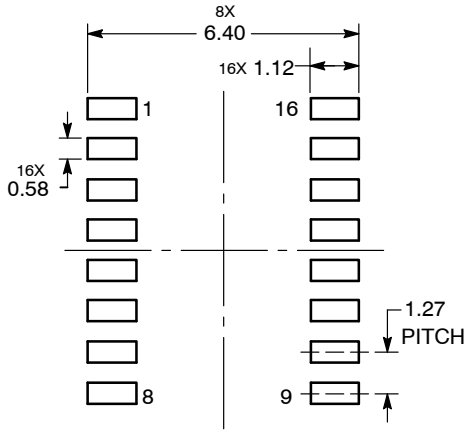
STYLE 4:
PIN 1. COLLECTOR, DYE #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. COLLECTOR, #3
6. COLLECTOR, #3
7. COLLECTOR, #4
8. COLLECTOR, #4
9. BASE, #4
10. EMITTER, #4
11. BASE, #3
12. EMITTER, #3
13. BASE, #2
14. EMITTER, #2
15. BASE, #1
16. EMITTER, #1

STYLE 5:
PIN 1. DRAIN, DYE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. DRAIN, #3
6. DRAIN, #3
7. DRAIN, #4
8. DRAIN, #4
9. GATE, #4
10. SOURCE, #4
11. GATE, #3
12. SOURCE, #3
13. GATE, #2
14. SOURCE, #2
15. GATE, #1
16. SOURCE, #1

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. CATHODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE
15. ANODE
16. ANODE

STYLE 7:
PIN 1. SOURCE N-CH
2. COMMON DRAIN (OUTPUT)
3. COMMON DRAIN (OUTPUT)
4. GATE P-CH
5. COMMON DRAIN (OUTPUT)
6. COMMON DRAIN (OUTPUT)
7. COMMON DRAIN (OUTPUT)
8. SOURCE P-CH
9. SOURCE P-CH
10. COMMON DRAIN (OUTPUT)
11. COMMON DRAIN (OUTPUT)
12. COMMON DRAIN (OUTPUT)
13. GATE N-CH
14. COMMON DRAIN (OUTPUT)
15. COMMON DRAIN (OUTPUT)
16. SOURCE N-CH

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

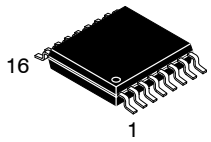
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MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

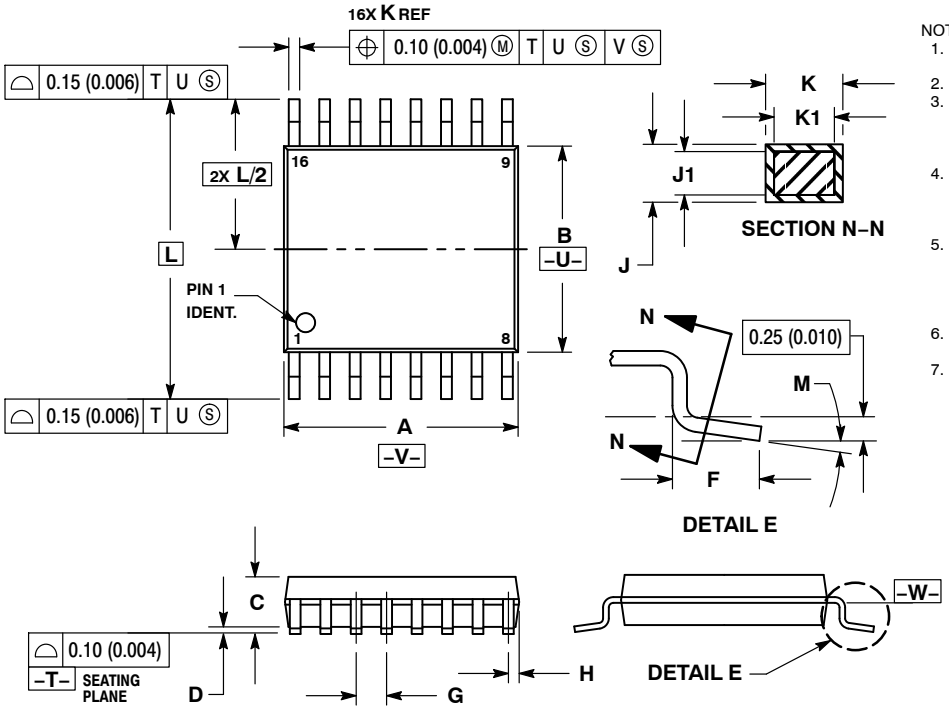
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SCALE 2:1

TSSOP−16
CASE 948F−01
ISSUE B

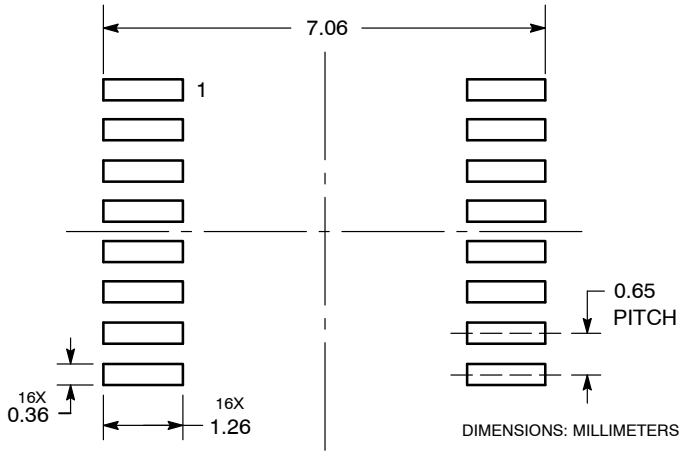
DATE 19 OCT 2006



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

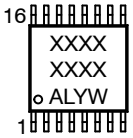
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXX	= Specific Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
G or ▪	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

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